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## What is claimed is:

- 1 1. An organic electroluminescence device comprising:
- 2 an anode;
- 3 an organic layer containing at least one organic light
- 4 emitting layer;
- 5 a cathode;
- 6 a cap used to encapsulate device main components having said
- 7 anode, said organic layer, and said cathode which are stacked on
- 8 an insulating substrate; and
- 9 wherein oxygen is contained in an interface between said
- 10 organic layer and said cathode.
  - 1 2. An organic electro luminescence device comprising:
  - 2 an anode;
- 3 an organic layer containing at least one organic light
- 4 emitting layer;
- 5 a cathode;
- 6 a cap used to encapsulate device main components having said
- 7 anode, said organic layer, and said cathode which are stacked on
- 8 an insulating substrate; and
- 9 wherein said cathode has a first cathode and a second
- 10 cathode and oxygen that is contained in an interface between said
- 11 organic layer and said first cathode.
- 1 3. An organic electro luminescence device comprising:
- 2 an anode;
- 3 an organic layer containing at least one organic light
- 4 emitting layer;

- 5 a cathode;
- a cap used to encapsulate device main components having said
- 7 anode, said organic layer, and said cathode which are stacked on
- 8 an insulating substrate; and
- 9 wherein said cathode has a plurality of layers and an oxygen
- 10 content in a first cathode contained in said plurality of layers
- 11 being in contact with said organic layer is larger than that in
- 12 any cathode formed on a second cathode and afterward being not
- 13 in contact with said organic layer.
  - 1 4. The organic electro luminescence device according to
  - 2 Claim 1, wherein a film thickness of said cathode is 20 nanometers
  - 3 to 100 nanometers.
  - 1 5. An organic EL according to claim 2, wherein a film
  - 2 thickness of said first cathode is 20nm to 100nm.
  - 1 6. The organic EL device according to Claim 3, wherein
  - 2 a film thickness of said first cathode is 20nm to 100nm.
  - 1 7. A method for manufacturing an organic EL device for
  - 2 encapsulating device main components having an anode, an organic
  - 3 layer containing at least one organic light emitting layer and
  - 4 a cathode which are formed on an insulating substrate using a cap,
  - 5 wherein said insulating substrate on which said device main
  - 6 components are formed are put into a vacuum apparatus before
  - 7 encapsulation and oxygen is contained in an interface between said
  - 8 organic layer and said cathode in a reduced pressure atmosphere.

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said anode;

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- A method for manufacturing an organic EL device for 1 8. encapsulating device main components having an anode, an organic 2 layer containing at least one organic light emitting layer and 3 cathodes consisting of a plurality of layers which are formed on 4 an insulating substrate using a cap, said method comprising; 5 a process of performing, after having formed a conductive 6 film on said insulating substrate, a patterning operation on a 7 conductive film so as to produce a desired shape in order to form 8
  - a process of putting said insulating substrate on which said anode has been formed into a vacuum apparatus and staking sequentially said organic layer and a first cathode contained in cathodes having a plurality of layers on said anode in a reduced pressure atmosphere;
- a process of introducing oxygen gas in said vacuum apparatus
  which said reduced pressure atmosphere maintained and causing
  said oxygen gas to be brought into contact with said first cathode;

a process of stacking cathodes to be formed after a second

- cathode has been formed on said first cathode in said reduced pressure atmosphere to form said device main components; and a process of encapsulating said device main components using said cap.
- 9. The method for manufacturing the organic EL device according to claim 7, wherein a film thickness of said first cathode is 20nm to 100nm.
- 1 10. The film manufacturing the organic EL device 2 according to Claim 8, wherein a film thickness of said first

- 3 cathode is 20nm to 100nm.
- 1 11. The method for manufacturing the organic EL device
- 2 according to claim 8, wherein said oxygen gas is introduced so
- 3 that a partial pressure of oxygen in said vacuum apparatus is 2
- 4  $\times$  10<sup>-4</sup> to 1  $\times$  10<sup>-1</sup> pascals.
- 1 12. The method for manufacturing the organic EL device
- 2 according to Claim 9, wherein said oxygen gas is introduced so
- 3 that a partial pressure oxygen in said vacuum apparatus is 2 imes
- 4  $10^{-4}$  to 1 x  $10^{-1}$  pascals.
- 1 13. The method for manufacturing the organic EL device
- 2 according to Claim 10, wherein said oxygen gas is introduced so
- $^{\rm 3}$   $\,$  that a partial pressure oxygen in said vacuum apparatus is 2  $_{\rm X}$
- $4 10^{-4} to 1 x 10^{-1} pascals.$
- 1 14. The method for manufacturing the organic EL device
- 2 according to Claim 7, wherein a vacuum evaporation apparatus is
- 3 used as said vacuum apparatus.